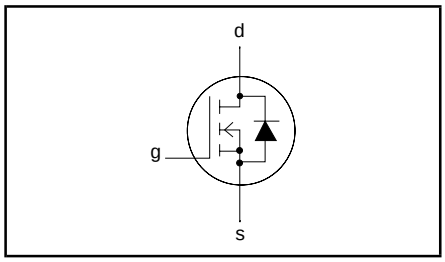
TrenchMOS™ transistor Logic level FET

PHP55N03LT, PHB55N03LT, PHD55N03LT

FEATURES

- **'Trench'** technology
- Very low on-state resistance
- Fast switching
- Stable off-state characteristics
- High thermal cycling performance
- Low thermal resistance

SYMBOL



QUICK REFERENCE DATA

V_{DSS} = 25 V

I_D = 55 A

$R_{DS(ON)} \leq 18\ m\Omega$ (V_{GS} = 5 V)

$R_{DS(ON)} \leq 14\ m\Omega$ (V_{GS} = 10 V)

GENERAL DESCRIPTION

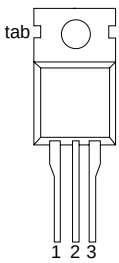
N-channel enhancement mode logic level field-effect power transistor in a plastic envelope using '**trench**' technology. The combination of very low on-state resistance and low switching losses make this device the optimum choice in high speed computer motherboard d.c. to d.c. converters.

The PHP55N03LT is supplied in the SOT78 (TO220AB) conventional leaded package.
The PHB55N03LT is supplied in the SOT404 surface mounting package.
The PHD55N03LT is supplied in the SOT428 surface mounting package.

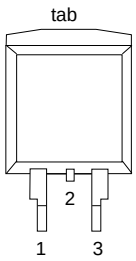
PINNING

PIN	DESCRIPTION
1	gate
2	drain[1]
3	source
tab	drain

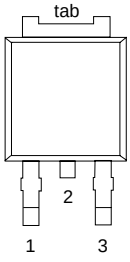
SOT78 (TO220AB)



SOT404



SOT428



LIMITING VALUES

Limiting values in accordance with the Absolute Maximum System (IEC 134)

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V_{DSS}	Drain-source voltage	T_j = 25 ˚C to 175˚C	-	25	V
V_{DGR}	Drain-gate voltage	T_j = 25 ˚C to 175˚C; R_{GS} = 20 kΩ	-	25	V
V_{GS}	Gate-source voltage		-	± 15	V
V_{GSM}	Pulsed gate-source voltage	$T_j \leq 150$˚C	-	± 20	V
I_D	Continuous drain current	T_{mb} = 25 ˚C; V_{GS} = 5 V	-	55	A
		T_{mb} = 100 ˚C; V_{GS} = 5 V	-	38	A
I_{DM}	Pulsed drain current	T_{mb} = 25 ˚C	-	220	A
P_D	Total power dissipation	T_{mb} = 25 ˚C	-	103	W
T_j, T_{stg}	Operating junction and storage temperature		- 55	175	˚C

1 It is not possible to make connection to pin 2 of the SOT428 or SOT404 packages.

THERMAL RESISTANCES

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
$R_{th\ j\text{-}mb}$	Thermal resistance junction to mounting base		-	-	1.45	K/W
$R_{th\ j\text{-}a}$	Thermal resistance junction to ambient	SOT78 package, in free air	-	60	-	K/W
		SOT404 and SOT428 packages, pcb mounted, minimum footprint	-	50	-	K/W

ELECTRICAL CHARACTERISTICS

T_j= 25˚C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
$V_{(BR)DSS}$	Drain-source breakdown voltage	V_{GS} = 0 V; I_D = 0.25 mA;	25	-	-	V
		T_j = -55˚C	22	-	-	V
$V_{GS(TO)}$	Gate threshold voltage	V_{DS} = V_{GS}; I_D = 1 mA	1	1.5	2	V
		T_j = 175˚C	0.5	-	-	V
		T_j = -55˚C	-	-	2.3	V
$R_{DS(ON)}$	Drain-source on-state resistance	V_{GS} = 10 V; I_D = 25 A	-	9	14	mΩ
		V_{GS} = 5 V; I_D = 25 A	-	13	18	mΩ
		V_{GS} = 5 V; I_D = 25 A; T_j = 175˚C	-	-	34	mΩ
g_{fs}	Forward transconductance	V_{DS} = 25 V; I_D = 25 A	10	20	-	S
I_{GSS}	Gate source leakage current	V_{GS} = ±5 V; V_{DS} = 0 V	-	10	100	nA
I_{DSS}	Zero gate voltage drain current	V_{DS} = 25 V; V_{GS} = 0 V;	-	0.05	10	µA
		T_j = 175˚C	-	-	500	µA
$Q_{g(tot)}$	Total gate charge	I_D = 20 A; V_{DD} = 24 V; V_{GS} = 10 V	-	52	-	nC
Q_{gs}	Gate-source charge		-	5.6	-	nC
Q_{gd}	Gate-drain (Miller) charge		-	14	-	nC
$t_{d\ on}$	Turn-on delay time	V_{DD} = 15 V; I_D = 25 A;	-	8.4	20	ns
t_r	Turn-on rise time	V_{GS} = 10 V; R_G = 5 Ω	-	63	100	ns
$t_{d\ off}$	Turn-off delay time	Resistive load	-	60	100	ns
t_f	Turn-off fall time		-	66	100	ns
L_d	Internal drain inductance	Measured tab to centre of die	-	3.5	-	nH
L_d	Internal drain inductance	Measured from drain lead to centre of die (SOT78 package only)	-	4.5	-	nH
L_s	Internal source inductance	Measured from source lead to source bond pad	-	7.5	-	nH
C_{iss}	Input capacitance	V_{GS} = 0 V; V_{DS} = 25 V; f = 1 MHz	-	1300	-	pF
C_{oss}	Output capacitance		-	430	-	pF
C_{rss}	Feedback capacitance		-	228	-	pF

REVERSE DIODE LIMITING VALUES AND CHARACTERISTICS

T_j = 25˚C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
I_S	Continuous source current (body diode)		-	-	55	A
I_{SM}	Pulsed source current (body diode)		-	-	220	A
V_{SD}	Diode forward voltage	I_F = 25 A; V_{GS} = 0 V I_F = 55 A; V_{GS} = 0 V	- -	0.95 1.0	1.2 -	V
t_{rr} Q_{rr}	Reverse recovery time Reverse recovery charge	I_F = 55 A; -dI_F/dt = 100 A/µs; V_{GS} = -10 V; V_R = 25 V	- -	70 0.1	- -	ns µC

AVALANCHE LIMITING VALUE

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
W_{DSS}	Drain-source non-repetitive unclamped inductive turn-off energy	I_D = 25 A; $V_{DD} \leq$ 15 V; V_{GS} = 5 V; R_{GS} = 50 Ω; T_{mb} = 25 ˚C	-	60	mJ

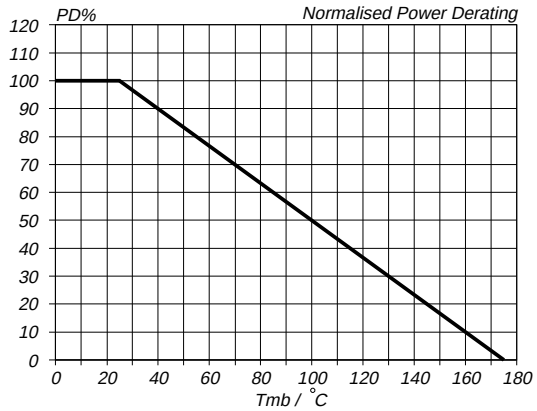


Fig.1. Normalised power dissipation.
PD% = 100·P_D/$P_{D\ 25\ ˚C}$ = f(T_{mb})

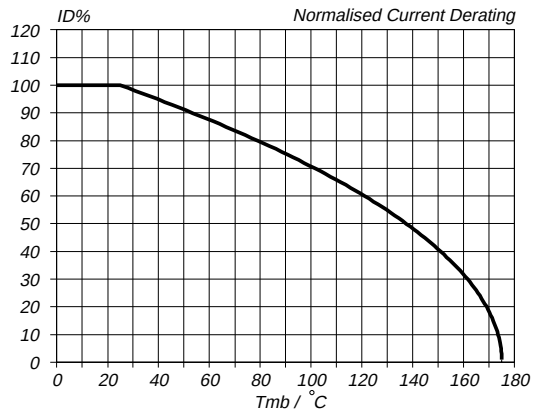


Fig.2. Normalised continuous drain current.
ID% = 100·I_D/$I_{D\ 25\ ˚C}$ = f(T_{mb}); conditions: $V_{GS} \geq$ 5 V

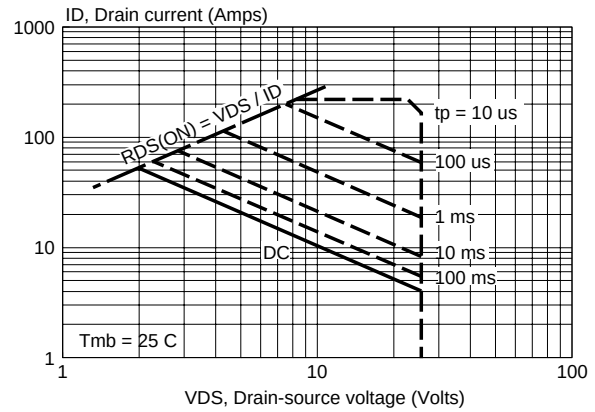


Fig.3. Safe operating area
I_D & I_{DM} = f(V_{DS}); I_{DM} single pulse; parameter t_p

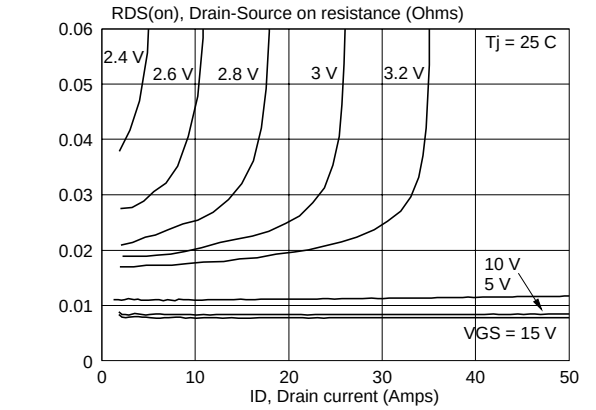


Fig.6. Typical on-state resistance, T_j = 25 ˚C.
$R_{DS(ON)}$ = f(I_D); parameter V_{GS}

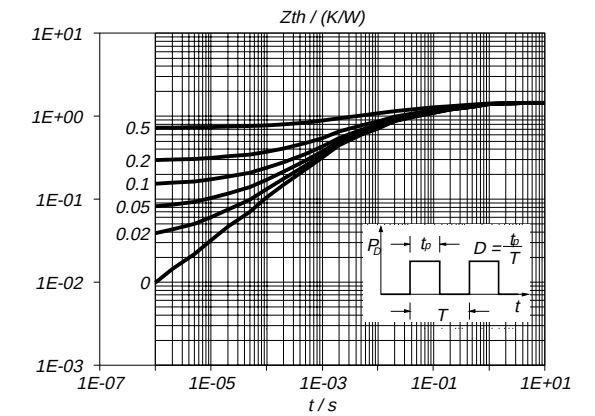


Fig.4. Transient thermal impedance.
$Z_{th\ j\text{-}mb}$ = f(t); parameter D = t_p/T

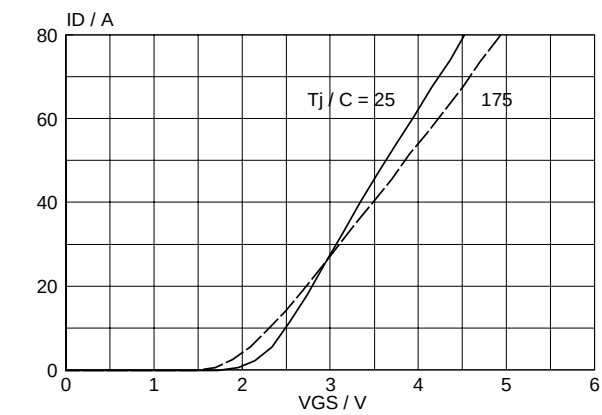


Fig.7. Typical transfer characteristics.
I_D = f(V_{GS}) ; conditions: V_{DS} = 25 V; parameter T_j

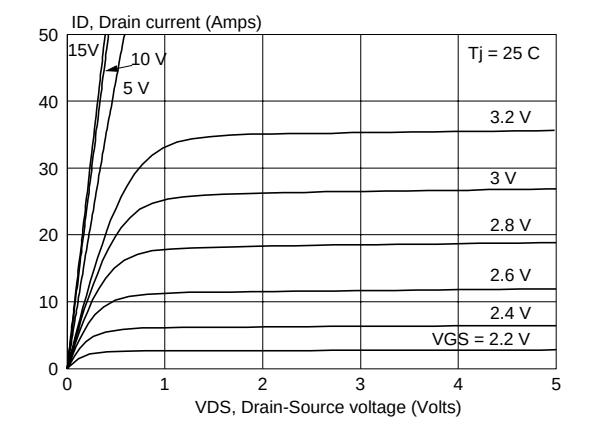


Fig.5. Typical output characteristics, T_j = 25 ˚C.
I_D = f(V_{DS}); parameter V_{GS}

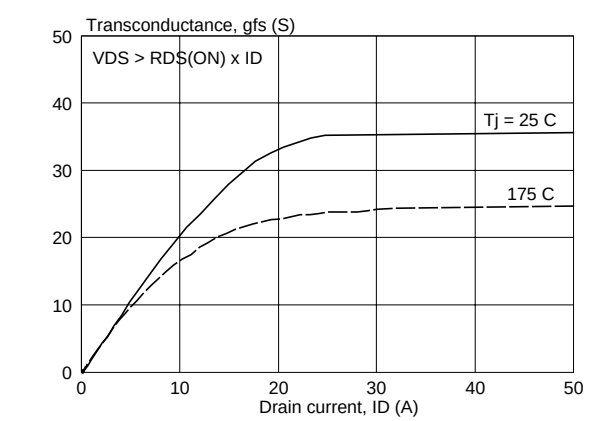


Fig.8. Typical transconductance, T_j = 25 ˚C.
g_{fs} = f(I_D); conditions: V_{DS} = 25 V

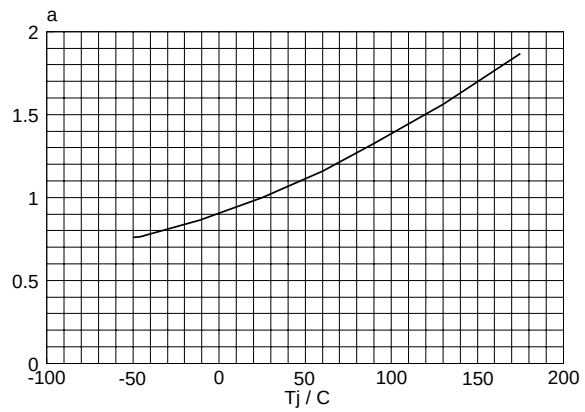


Fig.9. Normalised drain-source on-state resistance. $a = R_{DS(ON)}/R_{DS(ON)25\,^{\circ}C} = f(T_j)$

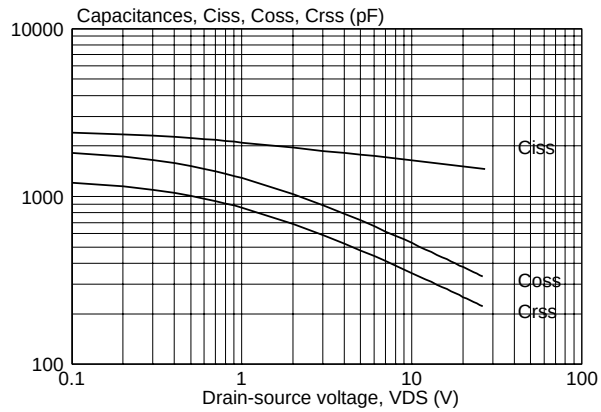


Fig.12. Typical capacitances, C_{iss}, C_{oss}, C_{rss}. $C = f(V_{DS})$; conditions: $V_{GS} = 0$ V; $f = 1$ MHz

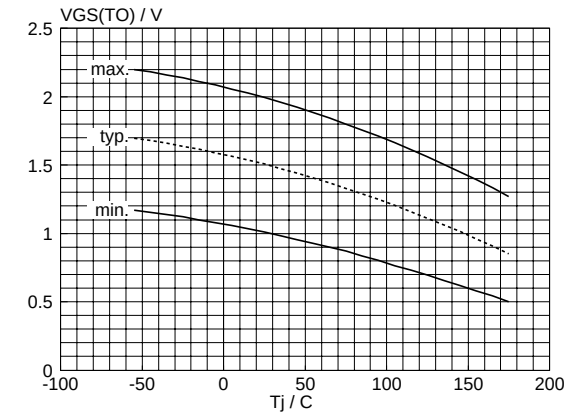


Fig.10. Gate threshold voltage. $V_{GS(TO)} = f(T_j)$; conditions: $I_D = 1$ mA; $V_{DS} = V_{GS}$

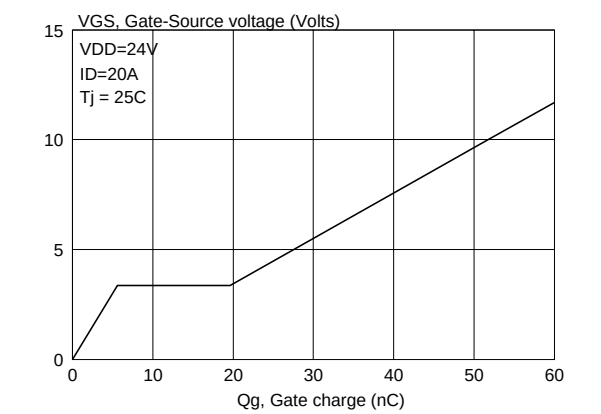


Fig.13. Typical turn-on gate-charge characteristics. $V_{GS} = f(Q_G)$; parameter V_{DS}

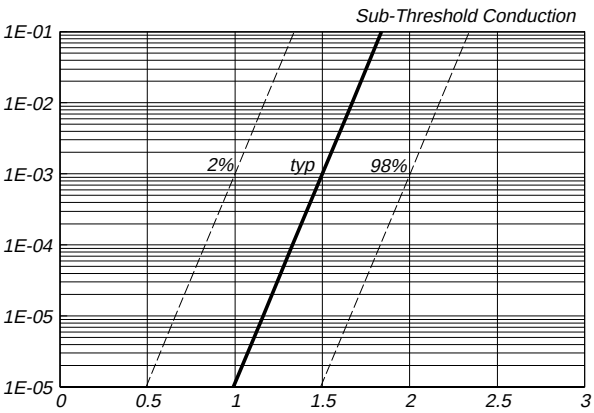


Fig.11. Sub-threshold drain current. $I_D = f(V_{GS})$; conditions: $T_j = 25$ ˚C; $V_{DS} = V_{GS}$

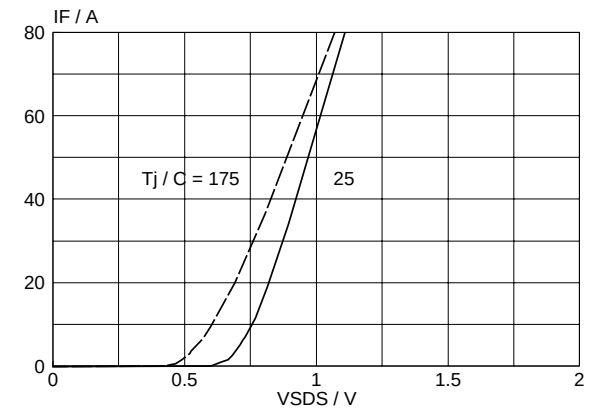


Fig.14. Typical reverse diode current. $I_F = f(V_{SDS})$; conditions: $V_{GS} = 0$ V; parameter T_j

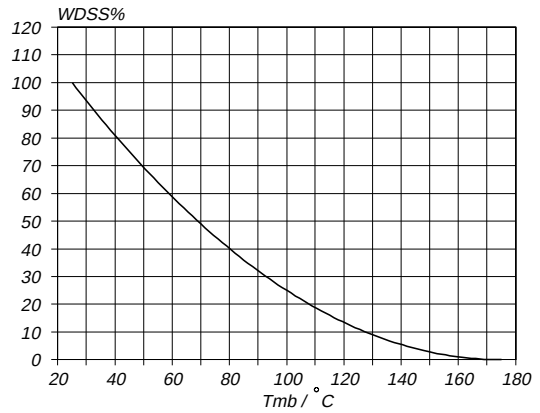


Fig.15. Normalised avalanche energy rating.
W_{DSS}% = f(T_{mb})

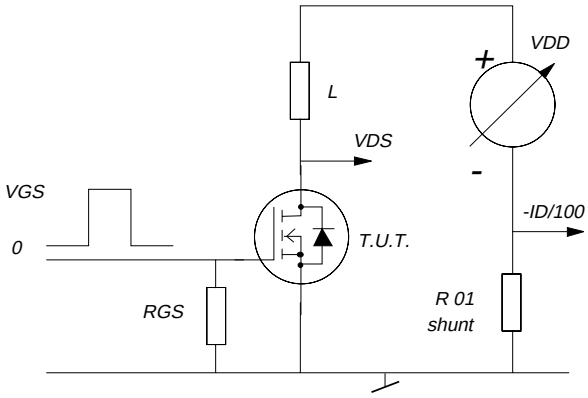


Fig.16. Avalanche energy test circuit.
$W_{DSS} = 0.5 \cdot L I_D^2 \cdot BV_{DSS}/(BV_{DSS} - V_{DD})$

MECHANICAL DATA

Dimensions in mm

Net Mass: 2 g

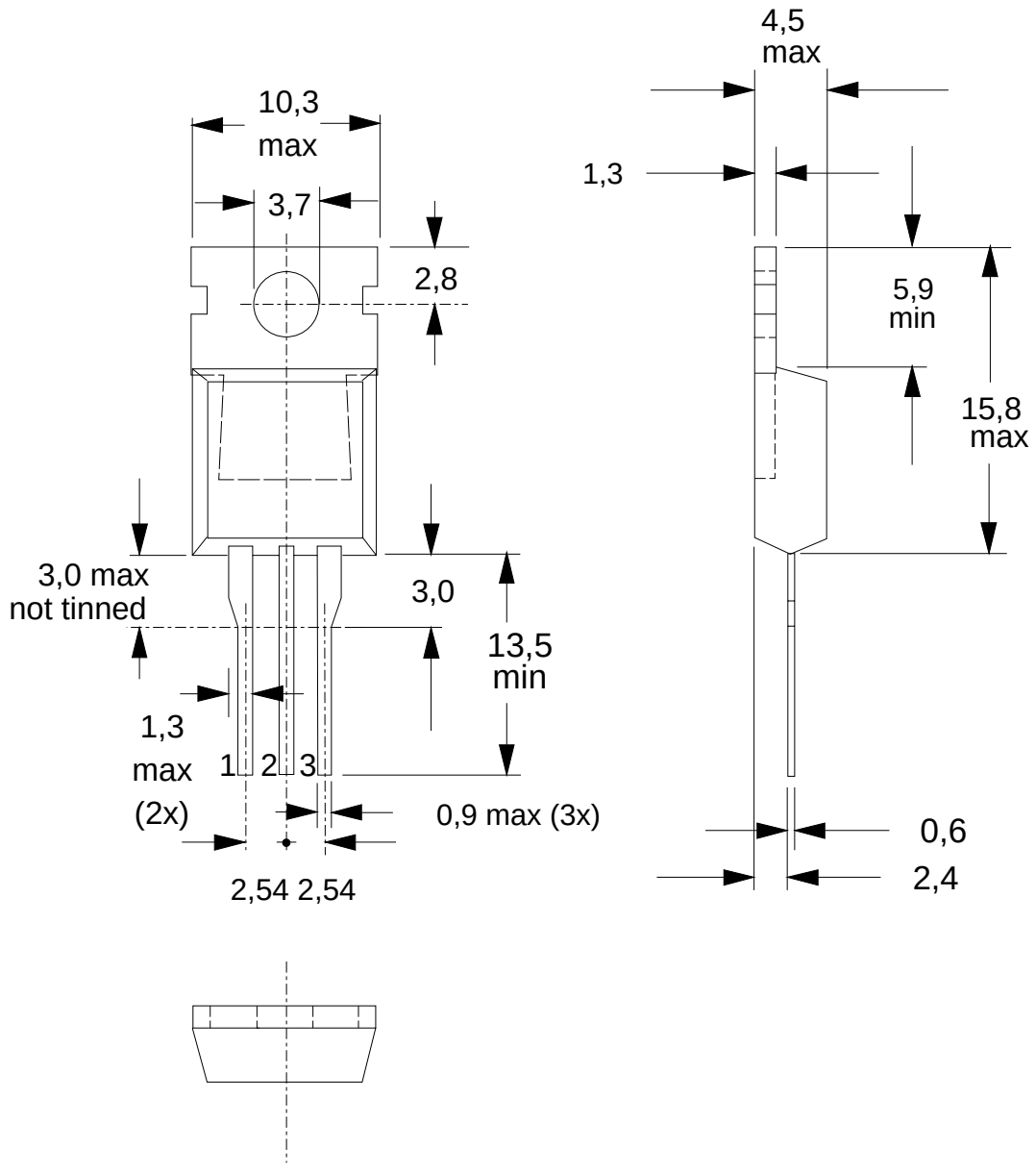


Fig.17. SOT78 (TO220AB); pin 2 connected to mounting base.

Notes

1. Observe the general handling precautions for electrostatic-discharge sensitive devices (ESDs) to prevent damage to MOS gate oxide.
2. Refer to mounting instructions for SOT78 (TO220) envelopes.
3. Epoxy meets UL94 V0 at 1/8".

MECHANICAL DATA

Dimensions in mm

Net Mass: 1.4 g

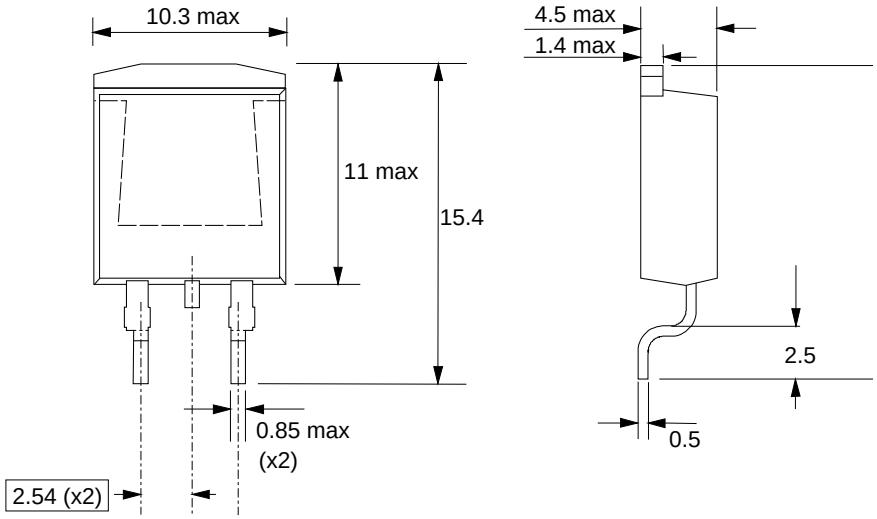


Fig.18. SOT404 : centre pin connected to mounting base.

MOUNTING INSTRUCTIONS

Dimensions in mm

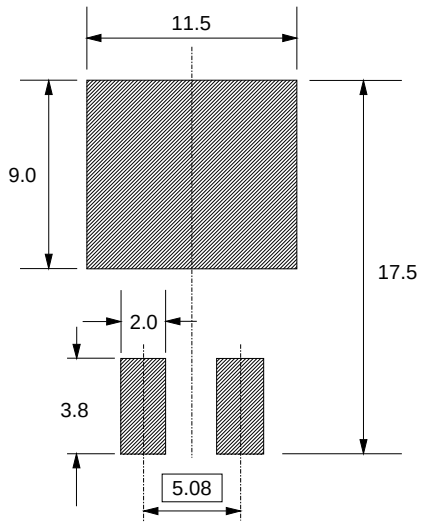


Fig.19. SOT404 : soldering pattern for surface mounting.

Notes

1. Observe the general handling precautions for electrostatic-discharge sensitive devices (ESDs) to prevent damage to MOS gate oxide.
2. Epoxy meets UL94 V0 at 1/8".

MECHANICAL DATA

Dimensions in mm : Net Mass: 1.4 g

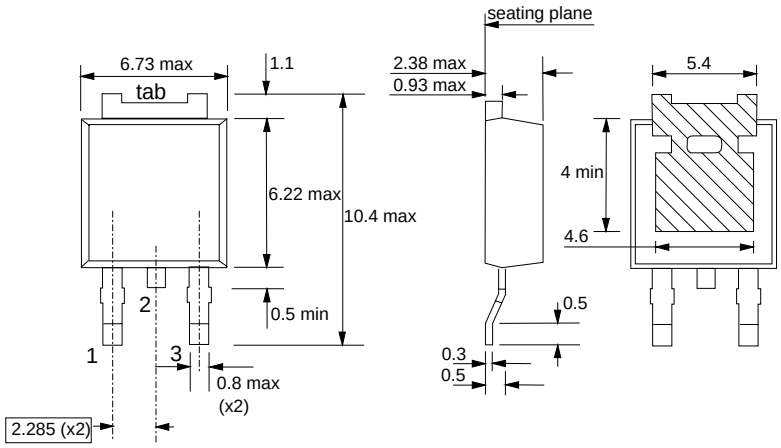


Fig.20. SOT428 : centre pin connected to mounting base.

MOUNTING INSTRUCTIONS

Dimensions in mm

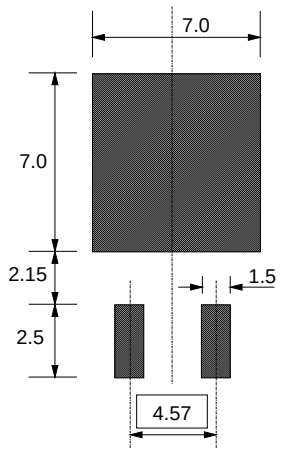


Fig.21. SOT428 : soldering pattern for surface mounting.

Notes

1. Observe the general handling precautions for electrostatic-discharge sensitive devices (ESDs) to prevent damage to MOS gate oxide.
2. Epoxy meets UL94 V0 at 1/8".

DEFINITIONS

Data sheet status	
Objective specification	This data sheet contains target or goal specifications for product development.
Preliminary specification	This data sheet contains preliminary data; supplementary data may be published later.
Product specification	This data sheet contains final product specifications.
Limiting values	
Limiting values are given in accordance with the Absolute Maximum Rating System (IEC 134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of this specification is not implied. Exposure to limiting values for extended periods may affect device reliability.	
Application information	
Where application information is given, it is advisory and does not form part of the specification.	

LIFE SUPPORT APPLICATIONS

These products are not designed for use in life support appliances, devices or systems where malfunction of these products can be reasonably expected to result in personal injury. Philips customers using or selling these products for use in such applications do so at their own risk and agree to fully indemnify Philips for any damages resulting from such improper use or sale.